# ES51C1A10V-20.000M



Nominal Frequency 20.000MHz

### ES51C1 A 10 V -20.000M

Control Voltage 1.5Vdc ±1.0Vdc

Series -RoHS Compliant (Pb-free) 5mm x 7mm Ceramic SMD 5.0Vdc Clipped Sinewave TC(VC)XO

Operating Temperature Range 0°C to +50°C

Frequency Stability -

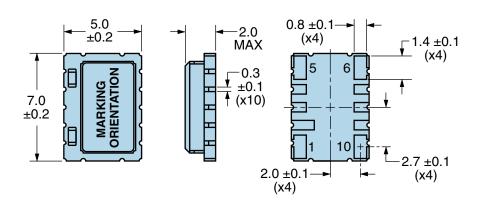
ELECTRICAL SPECIFICA	TIONS
Nominal Frequency	20.000MHz
Frequency Stability vs. Frequency Tolerance	±1.0ppm Maximum (Measured at 25°C ±2°C, Vdd=5.0Vdc, Vc=1.5Vdc)
Frequency Stability	±1.0ppm Maximum
Frequency Stability vs. Input Voltage	±0.2ppm Maximum (Vdd ±5%)
Frequency Stability vs. Aging	±1ppm/Year Maximum (at 25°C)
Frequency Stability vs. Load	±0.2ppm Maximum (±1kOhm//±1pF)
Operating Temperature Range	0°C to +50°C
Supply Voltage	5.0Vdc ±5%
Input Current	2.0mA Maximum
Output Voltage	0.8Vp-p Clipped Sinewave Minimum
Load Drive Capability	10kOhms//10pF
Output Logic Type	Clipped Sinewave
Control Voltage	1.5Vdc ±1.0Vdc
Frequency Deviation	±8ppm Minimum
Linearity	10% Maximum
Transfer Function	Positive Transfer Characteristic
Modulation Bandwidth	3kHz Minimum (Measured at -3dB with a Control Voltage of 1.5Vdc)
Input Impedance	100kOhms Minimum
Phase Noise	-80dBc/Hz at 10Hz offset, -115dBc/Hz at 100Hz offset, -135dBc/Hz at 1kHz offset, -145dBc/Hz at 10kHz offset, -145dBc/Hz at 10kHz offset, -145dBc/Hz at 10kHz offset (Typical Values, at 12.800MHz)
Start Up Time	5mSec Maximum
Storage Temperature Range	-55°C to +125°C

Fine Leak Test	MIL-STD-883, Method 1014 Condition A	
Gross Leak Test	MIL-STD-883, Method 1014 Condition C	
Mechanical Shock	MIL-STD-202, Method 213 Condition C	
Resistance to Soldering Heat	MIL-STD-202, Method 210	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010	
Vibration	MIL-STD-883, Method 2007 Condition A	

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### **MECHANICAL DIMENSIONS (all dimensions in millimeters)**



PIN	CONNECTION
1	Voltage Control
2	Do Not Connect
3	Do Not Connect
4	Do Not Connect
5	Case/Ground
6	Output
7	Do Not Connect
8	Do Not Connect
9	Do Not Connect
10	Supply Voltage
LINE	MARKING
1	<b>E20.000</b> <i>E=Ecliptek</i>
2	XXYZZ XX=Ecliptek Manufacturing Code Y=Last Digit of the Year ZZ=Week of the Year

#### Suggested Solder Pad Layout

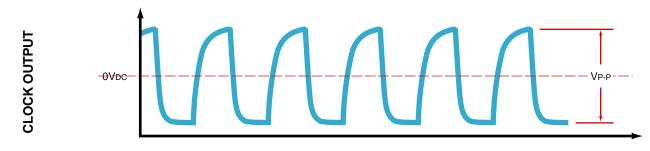
All Dimensions in Millimeters  $\rightarrow$  1.2 (X4) 1.8 (X4) 3.9 3.0 3.0 3.0 4 3.0 4 3.0 4 4 3.0 4 3.0 4 4 4 1.8 (X4) 1.8 (X

All Tolerances are ±0.1

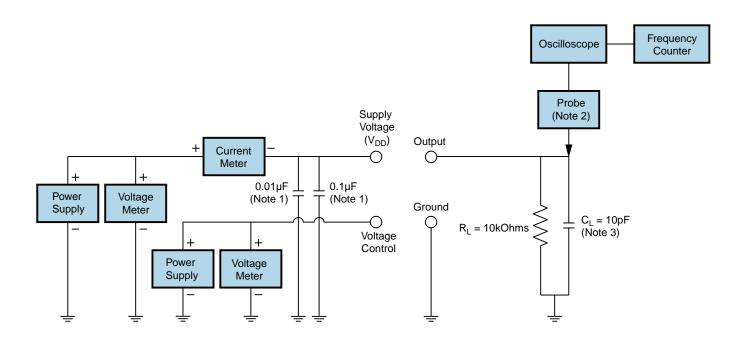
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**OUTPUT WAVEFORM** 



#### **Test Circuit for Voltage Control Option**



Note 1: An external 0.1  $\mu F$  low frequency tantalum bypass capacitor in parallel with a 0.01  $\mu F$  high frequency ceramic bypass capacitor close to the package ground and V\_{DD} pin is required.

Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.



## **Recommended Solder Reflow Methods**

ES51C1A10V-20.000M



### Low Temperature Infrared/Convection 220°C

T <sub>s</sub> MAX to T <sub>L</sub> (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T <sub>s</sub> MIN)	N/A
- Temperature Typical (T <sub>s</sub> TYP)	150°C
- Temperature Maximum (T <sub>s</sub> MAX)	N/A
- Time (t <sub>s</sub> MIN)	60 - 120 Seconds
Ramp-up Rate (T⊾ to T <sub>P</sub> )	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T <sub>P</sub> )	220°C Maximum
Target Peak Temperature (T <sub>P</sub> Target)	220°C Maximum 1 Time / 215°C Maximum 1 Time
Time within 5°C of actual peak (t <sub>p</sub> )	15 seconds Maximum 1 Time / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1

#### Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum.

#### **High Temperature Manual Soldering**

260°C Maximum for 5 seconds Maximum, 2 times Maximum.